

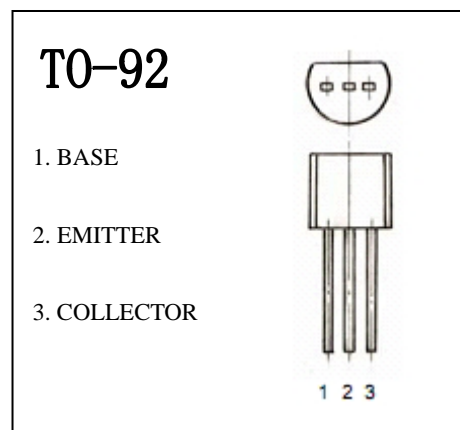
# 深圳市晶泰源电子有限公司

2SC3355

TRANSISTOR(NPN)

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	20	V
VCEO	Collector-Emitter Voltage	12	V
VEBO	Emitter-Base Voltage	3	V
IC	Collector Current	0.1	A
PC	Collector Power Dissipation	600	mW
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=100uA, IE=0	20			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=1mA, IB=0	12			V
Emitter-base breakdown voltage	V(BR)EBO	IC=100uA, IC=0	3			V
Collector cut-off current	ICBO	VCB=10V, IE=0			0.1	μA
Emitter cut-off current	IEBO	VEB=1V, IC=0			0.1	μA
DC current gain	HFE	Vce=10V, IC=20mA	50	120	300	
Collector-emitter saturation voltage	VCE(sat)	IC=10mA, IB=1mA			0.5	V
Transition frequency	fT	VCE=10V, IC=20mA		6.5		MHz
Noise Figure(1)	NF	VCE=10V, IC=7mA, f=1GHZ		1.1		dB
Noise Figure(2)	NF	VCE=10V, IC=40mA, f=1GHZ		1.8	3.0	dB
Collector output capacitance	Cob	VCB=10V, IE=0, f=1MHz		0.65	1.0	pF